



**ALPHA & OMEGA**  
SEMICONDUCTOR

**AO6403**

**P-Channel Enhancement Mode Field Effect Transistor**



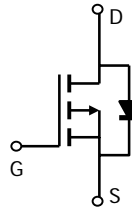
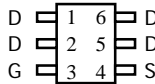
**General Description**

The AO6403 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , and ultra-low low gate charge. This device is suitable for use as a load switch or in PWM applications. It may be used in common-drain configuration to form a bidirectional blocking switch. *AO6403 is Pb-free (meets ROHS & Sony 259 specifications). AO6403L is a Green Product ordering option. AO6403 and AO6403L are electrically identical.*

**Features**

$V_{DS} (V) = -30V$   
 $I_D = -6 A (V_{GS} = -10V)$   
 $R_{DS(ON)} < 35m\Omega (V_{GS} = -10V)$   
 $R_{DS(ON)} < 58m\Omega (V_{GS} = -4.5V)$

TSOP6  
Top View



**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	-6	A
		-5	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-30	
Power Dissipation <sup>A</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	2	W
		1.44	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	47.5	62.5	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	74	
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	37	50	$^\circ C/W$

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1.2	-2	-2.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-6\text{A}$ $T_J=125^\circ\text{C}$		28 37	35 45	m $\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-5\text{A}$		44	58	
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-6\text{A}$		13		S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.76	-1	V
$I_S$	Maximum Body-Diode Continuous Current				-4.2	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		920		pF
$C_{oss}$	Output Capacitance			190		pF
$C_{rss}$	Reverse Transfer Capacitance			122		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		3.6		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, I_D=-6\text{A}$		18.5		nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			9.6		nC
$Q_{gs}$	Gate Source Charge			2.7		nC
$Q_{gd}$	Gate Drain Charge			4.5		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, R_L=2.7\Omega,$ $R_{GEN}=3\Omega$		7.7		ns
$t_r$	Turn-On Rise Time			5.7		ns
$t_{D(off)}$	Turn-Off Delay Time			20.2		ns
$t_f$	Turn-Off Fall Time			9.5		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-6\text{A}, dI/dt=100\text{A}/\mu\text{s}$		20		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-6\text{A}, dI/dt=100\text{A}/\mu\text{s}$		8.8		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

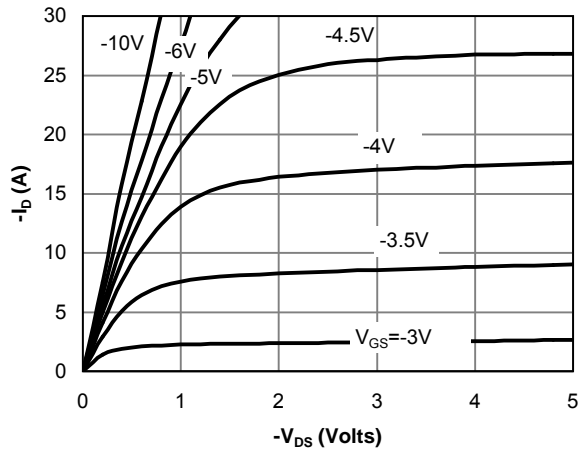


Fig 1: On-Region Characteristics

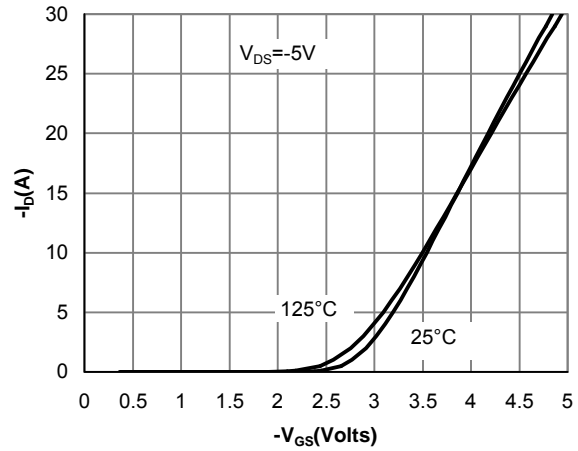


Figure 2: Transfer Characteristics

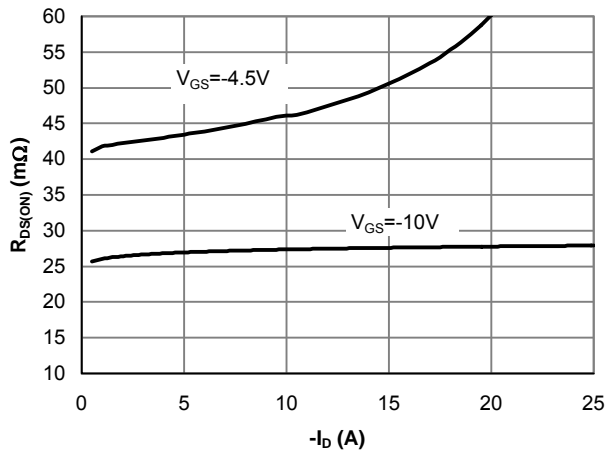


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

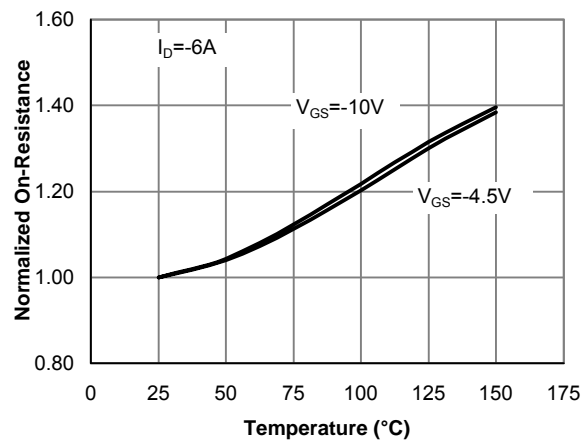


Figure 4: On-Resistance vs. Junction Temperature

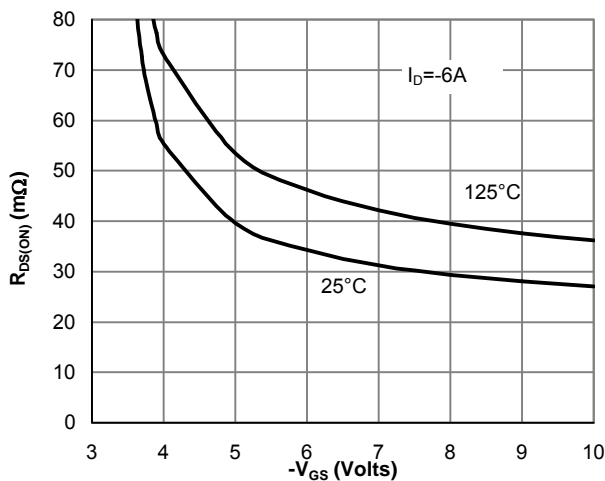


Figure 5: On-Resistance vs. Gate-Source Voltage

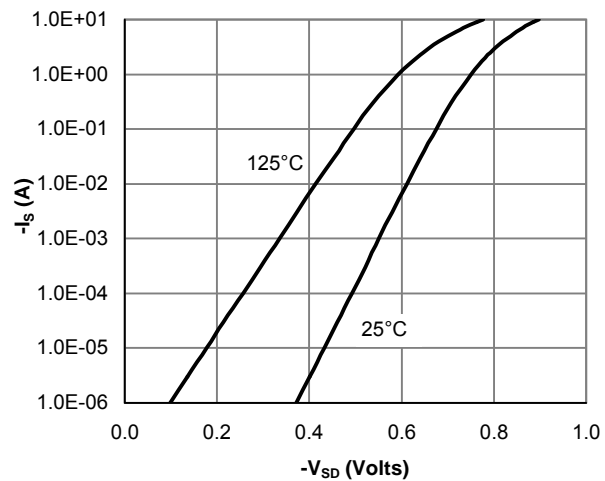


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

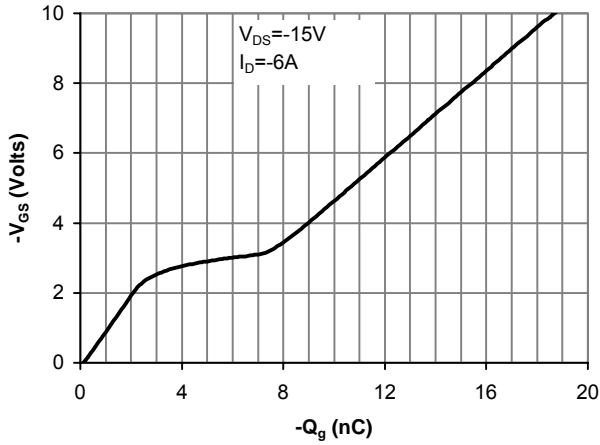


Figure 7: Gate-Charge Characteristics

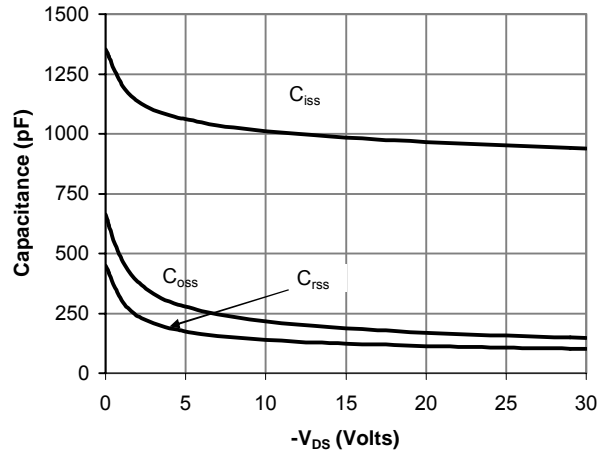


Figure 8: Capacitance Characteristics

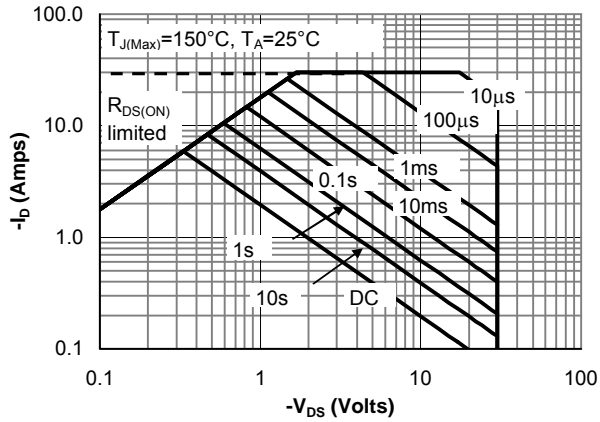


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

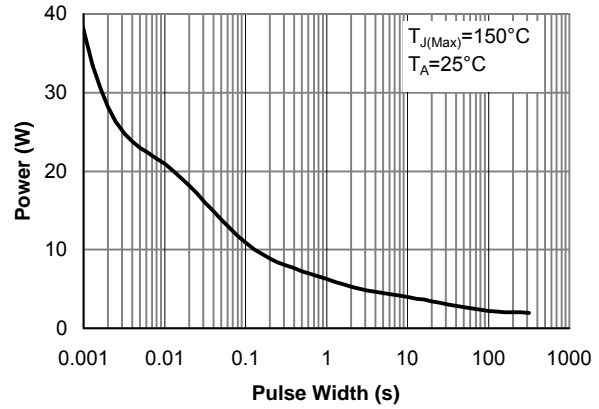


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

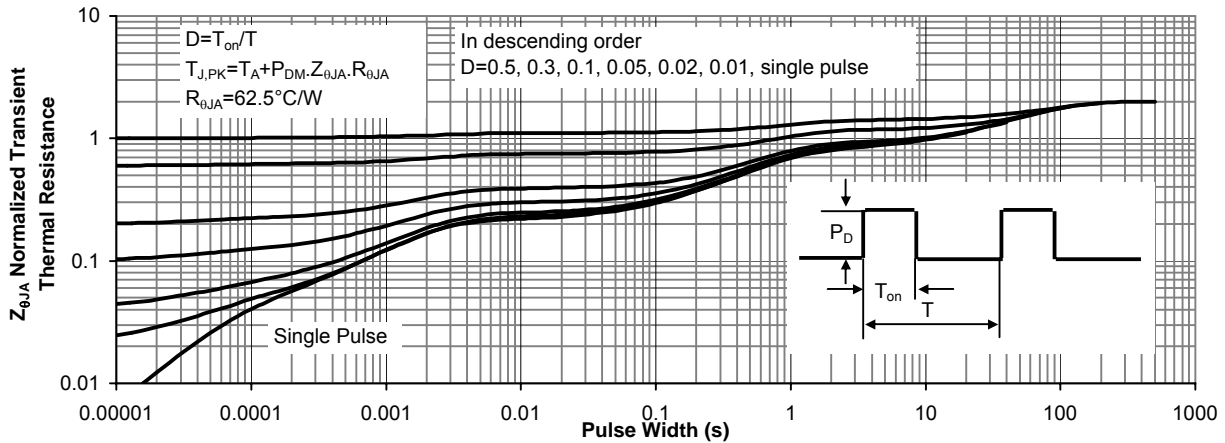


Figure 11: Normalized Maximum Transient Thermal Impedance